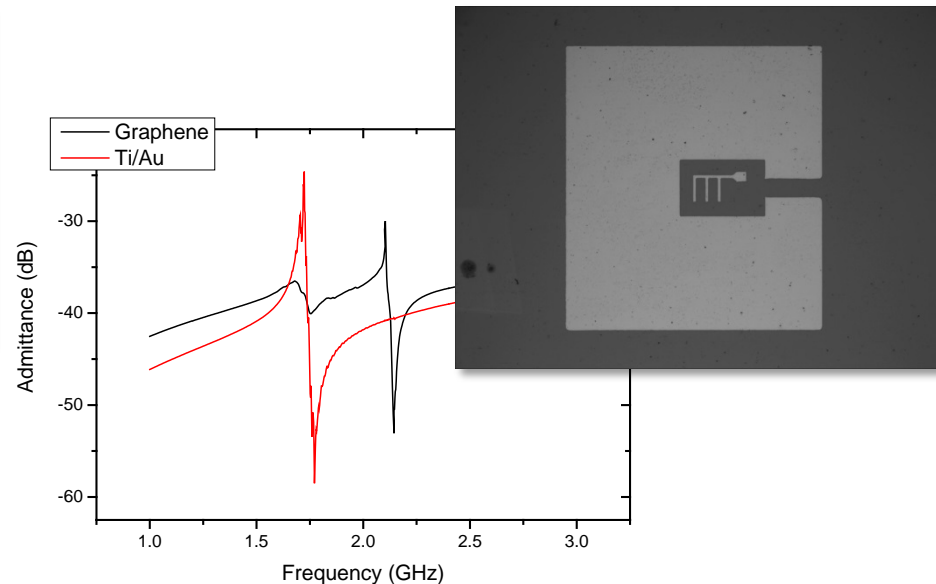
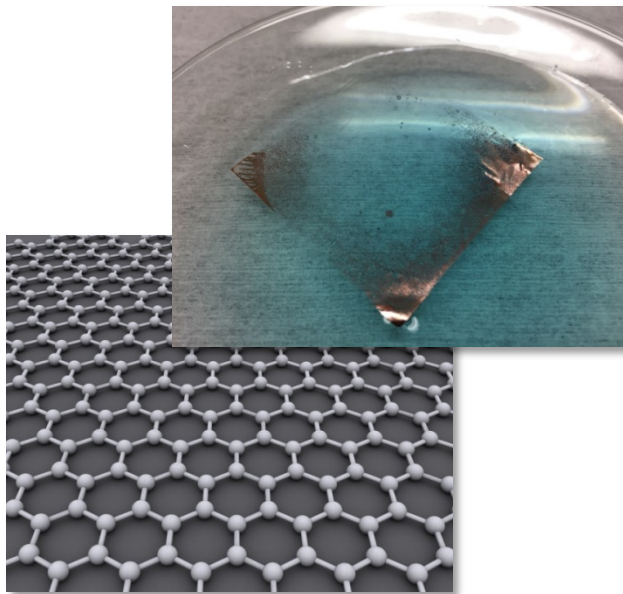


GRAPHENE AS VIRTUALLY MASSLESS TOP ELECTRODE FOR RF BULK ACOUSTIC WAVE (BAW) RESONATORS

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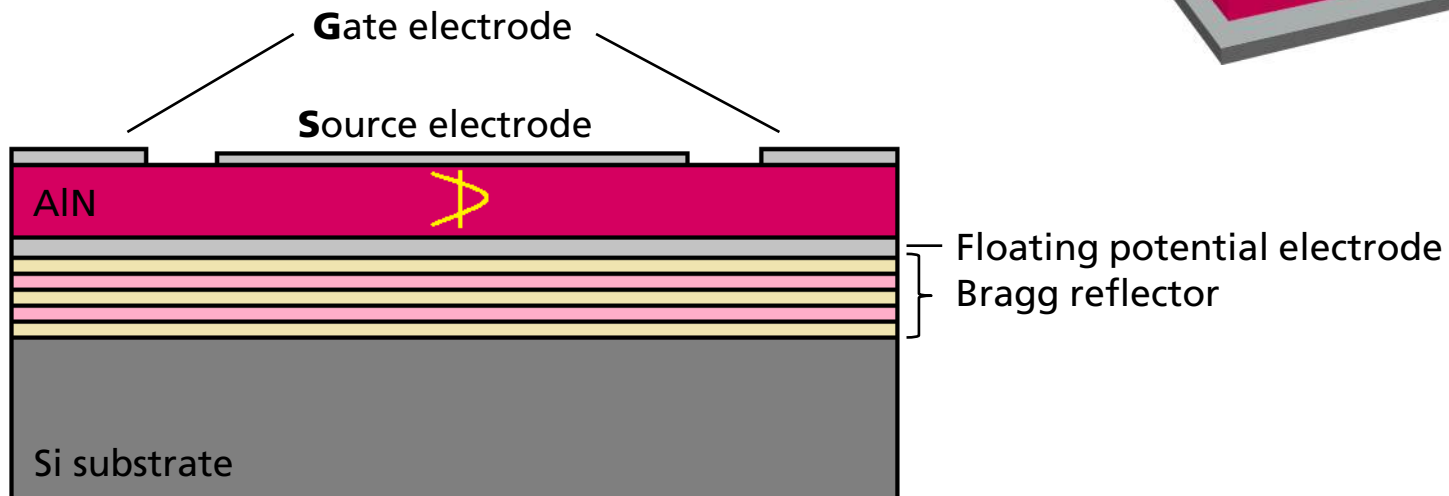
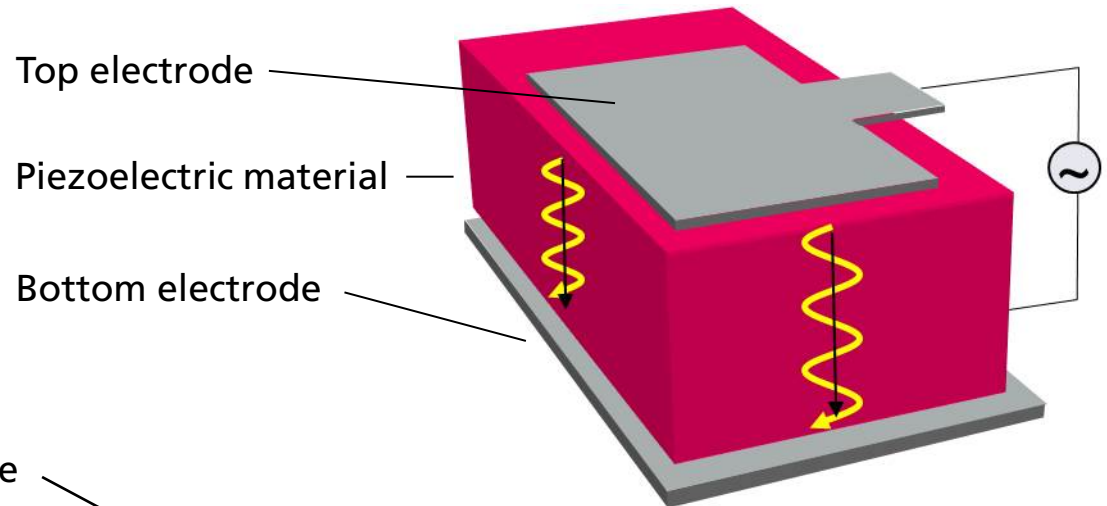
Motivation

- BAW resonators are key-building blocks for radio frequency (RF) filters used in wireless communication devices (e.g. smartphones)



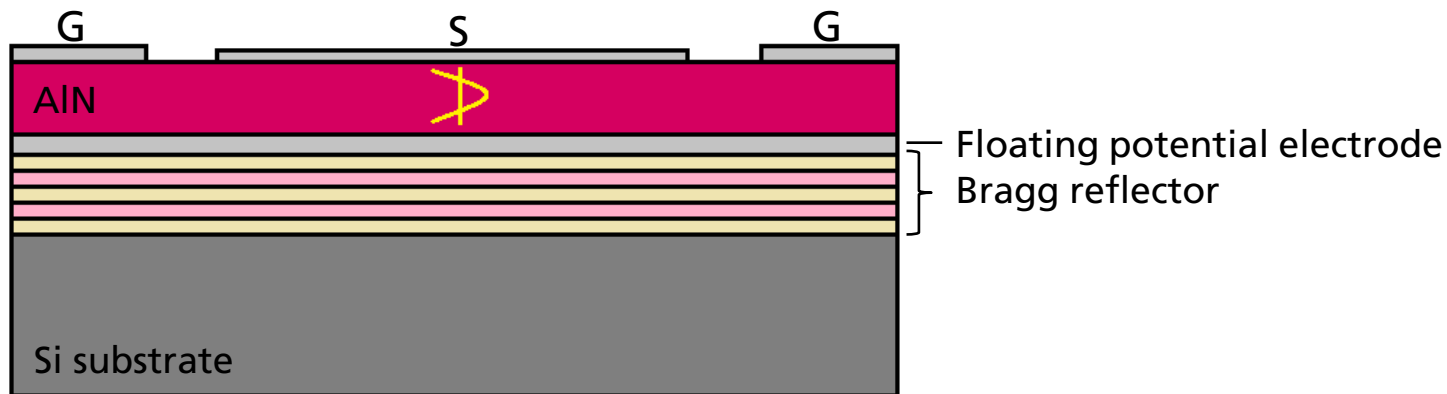
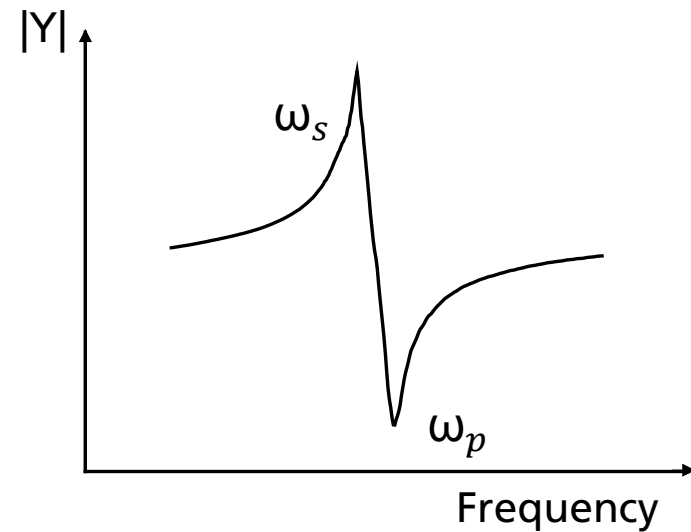
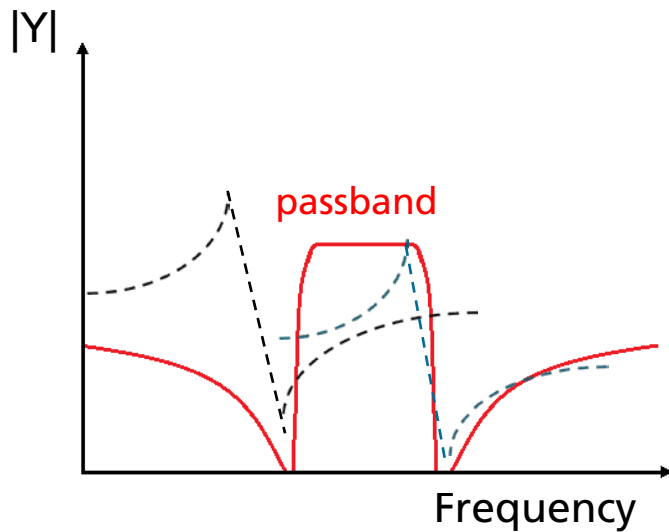
Source: Oleksiy mark - Fotolia

Bulk acoustic wave (BAW) resonator



Solidly mounted resonator (SMR)

Bulk acoustic wave (BAW) resonator



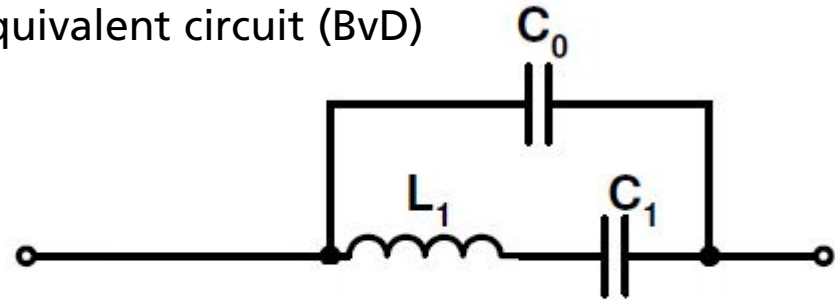
BAW-SMR

Bulk acoustic wave (BAW) resonator

$$\omega_s = \frac{1}{\sqrt{L_1 C_1}}$$

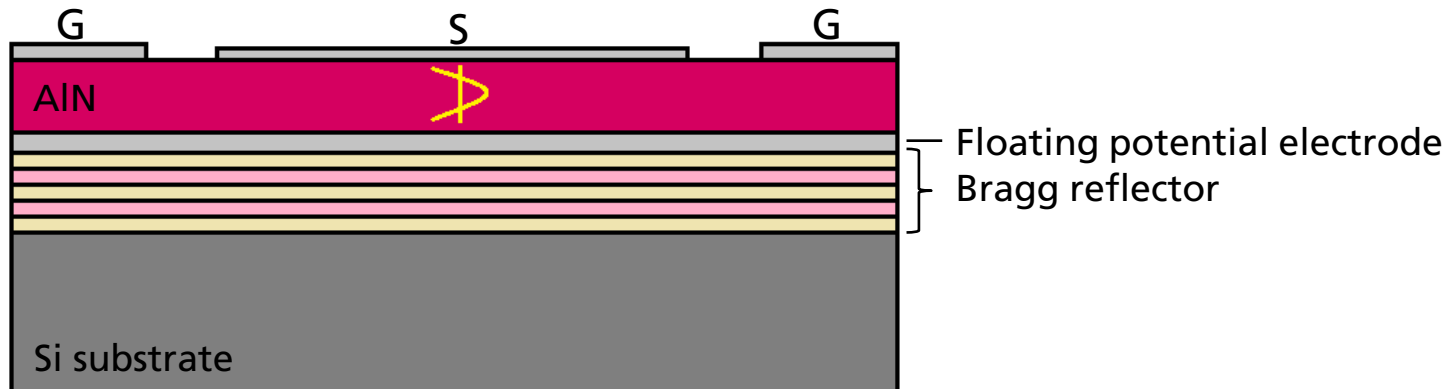
$$\omega_p = \frac{1}{\sqrt{L_1 C_1}} \sqrt{1 + \frac{C_1}{C_0}}$$

Equivalent circuit (BvD)



C_0 : total plate capacitance

L_1, C_1 : mechanical resonator branch

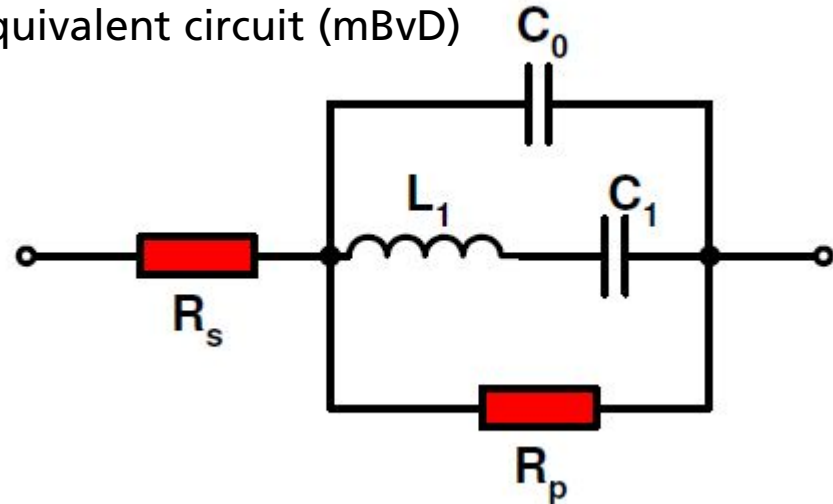


BAW-SMR

Electrode induced electrical and mechanical losses in BAW resonators

- Parallel resistor R_p represents viscous and dielectric losses (**non-zero electrode mass**)
- Serial resistor R_s represents ohmic losses (**non-zero electrode resistance**)

Equivalent circuit (mBvD)

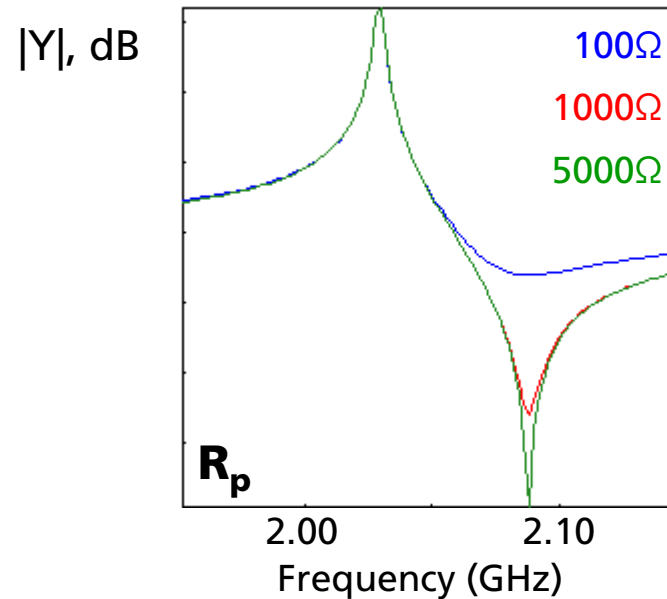
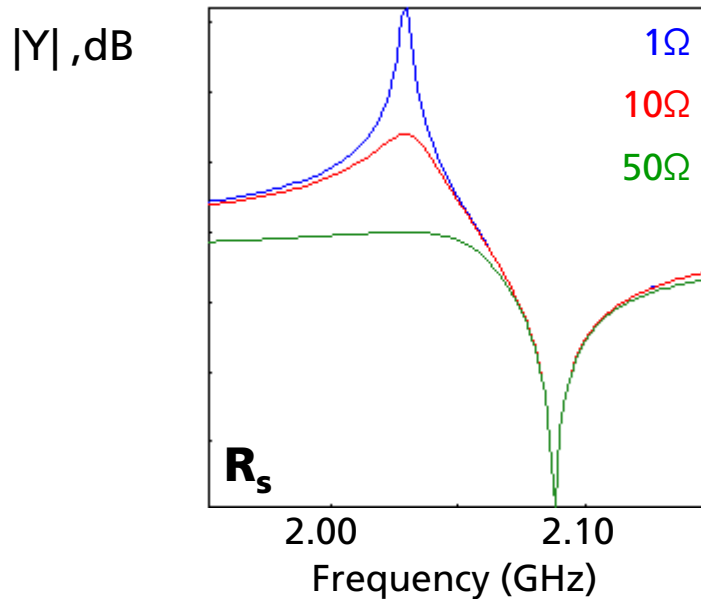


Q factor as main resonator characteristic

$$Q_s = \frac{1}{R_s} \sqrt{\frac{L_1}{C_1}}$$

$$Q_p = \omega_p R_p \frac{C_1 + C_0}{C_1} C_0$$

Influence of R_s and R_p on admittance curves



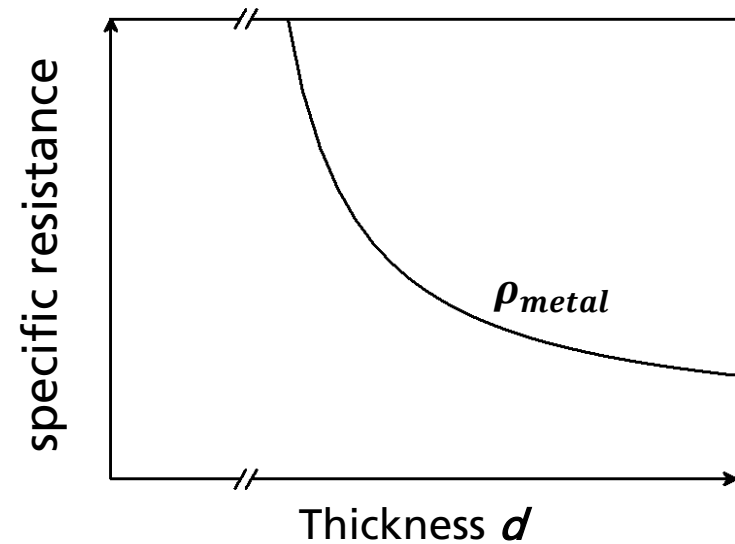
- Resonance peak sharpness indicates Q factor
- Q strongly depends on losses

Idea: thin conductive electrodes to reduce viscous losses

Graphene as massless electrode – Fuchs-Sondheimer model

■ Fuchs-Sondheimer model

$$\rho_{ges} = \rho_{bulk} + \rho_{SS}, \rho_{SS} \sim \left(1 + \frac{1}{d \cdot \ln \frac{1}{d}}\right) * \rho_{bulk}$$



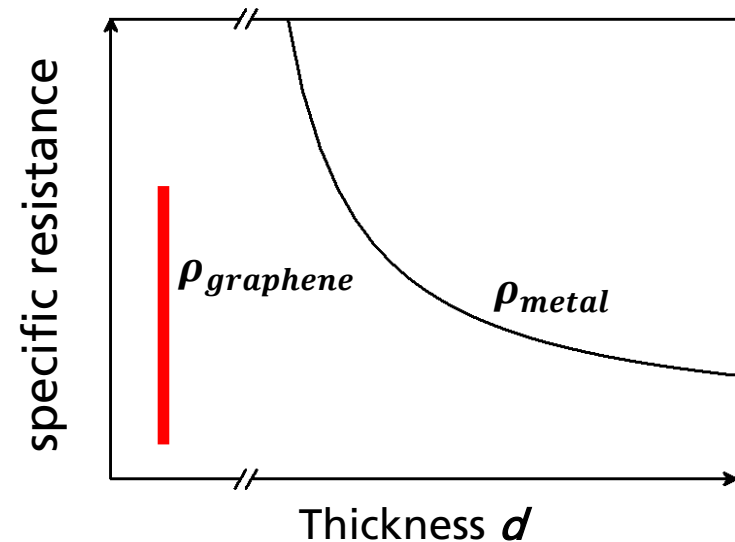
Graphene as massless electrode – Fuchs-Sondheimer model

- Fuchs-Sondheimer model

$$\rho_{ges} = \rho_{bulk} + \rho_{SS}, \rho_{SS} \sim \left(1 + \frac{1}{d \cdot \ln \frac{1}{d}}\right) * \rho_{bulk}$$

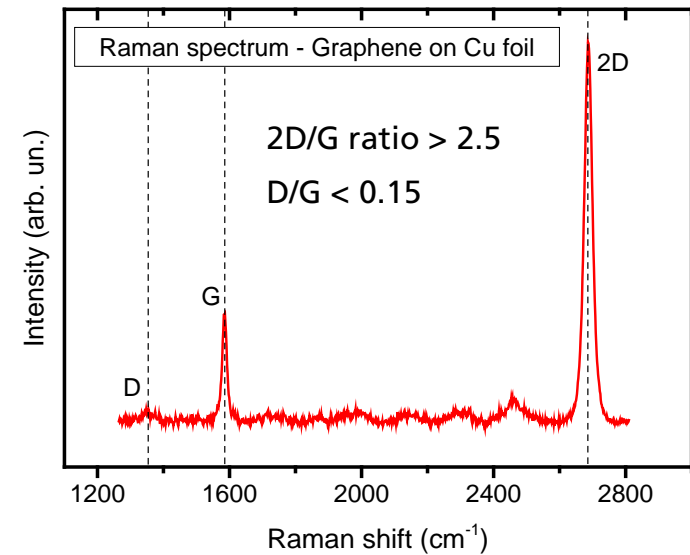
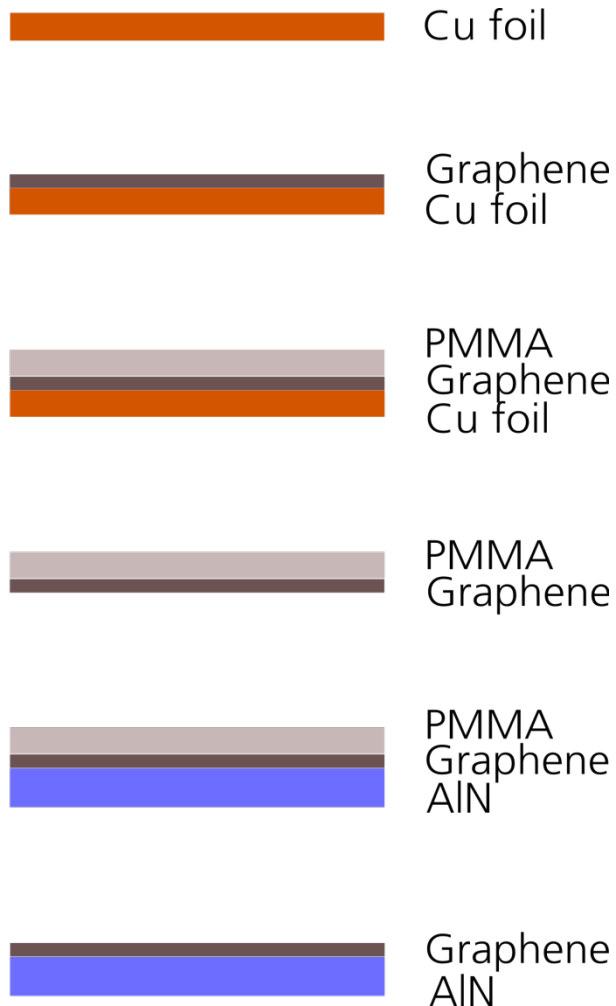
- Graphene is virtually massless, still conductive

➔ Reduction of viscous losses!



Replacement of conventional metal electrodes (Ti/Au) with graphene

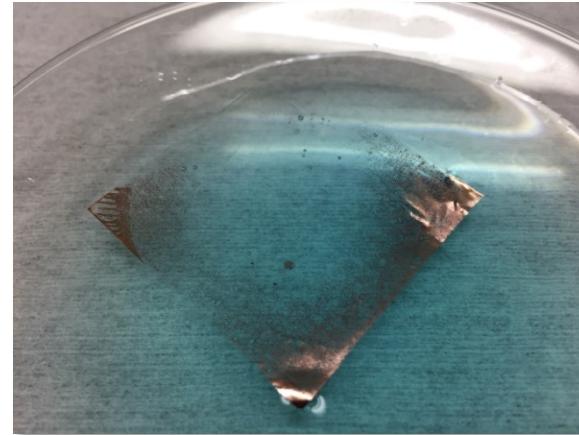
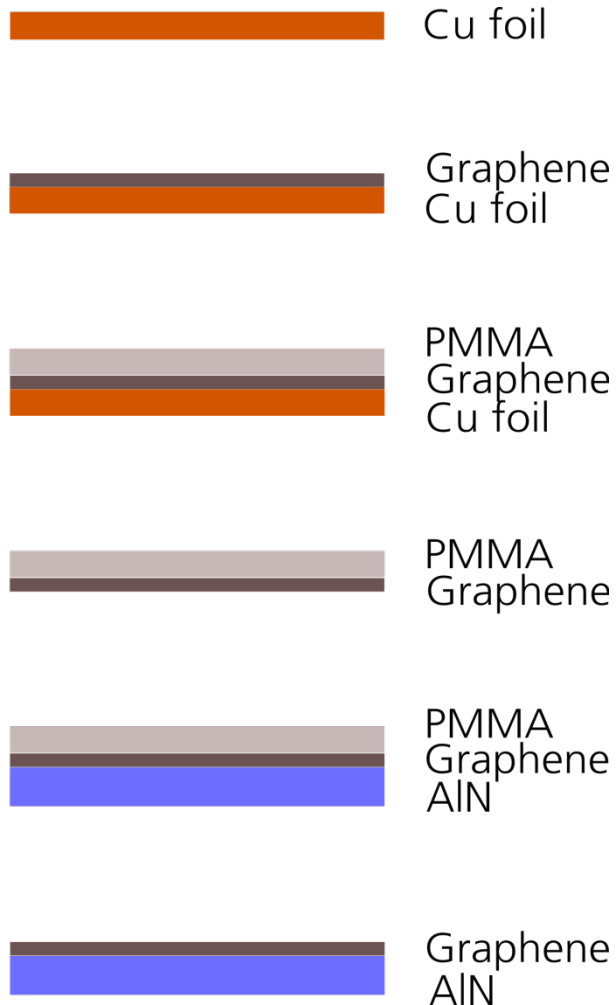
Process development – Graphene growth and transfer



■ Standard CVD process

- Aixtron BlackMagic CVD reactor
- Methane as precursor, H_2 as carrier gas
- Cu foil as catalytic substrate

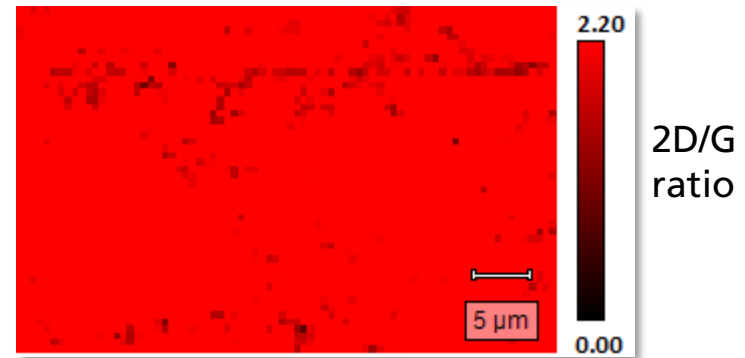
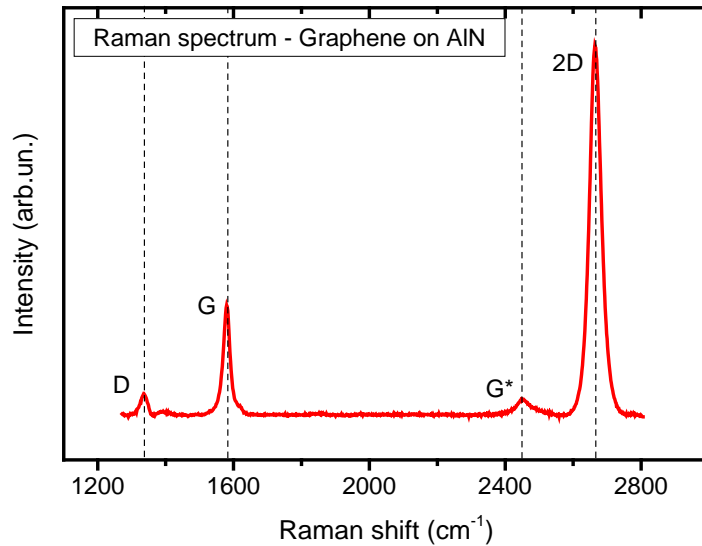
Process development – Graphene growth and transfer



Cufoil etching in APS

- Graphene wet transfer process
 - Poly (methyl methacrylate) (PMMA) as protection layer
 - Cu foil etching in Ammonium persulfate (APS)

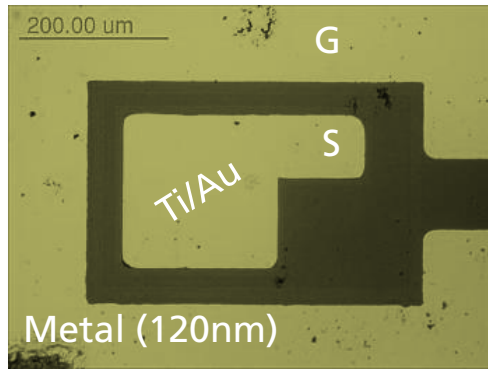
Process development – Graphene growth and transfer



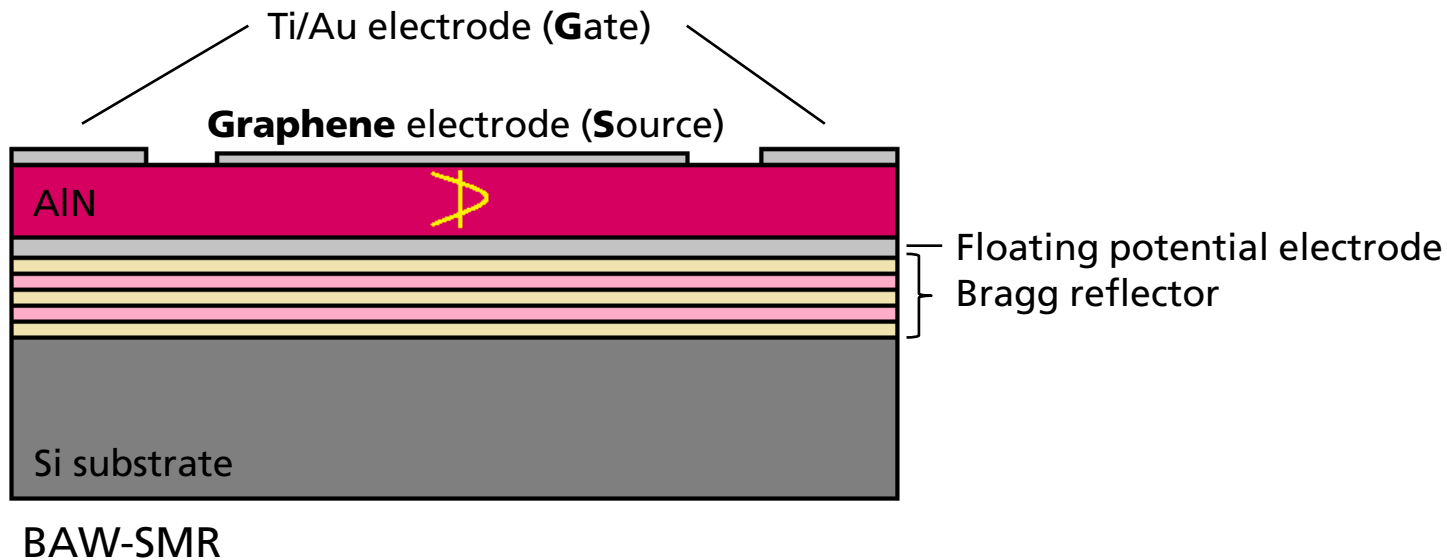
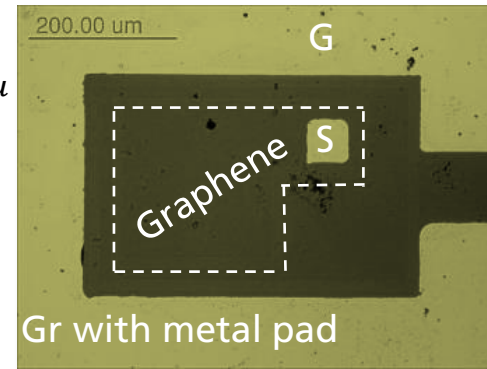
- Sheet resistance of graphene on AlN via 4-point-measurement:

40 x 40 mm ²	Reproducible $R_S < 2k\Omega$
40 x 40 mm ²	Best $R_S \approx 350\Omega$
15 x 10 mm ²	Best $R_S \approx 280\Omega$

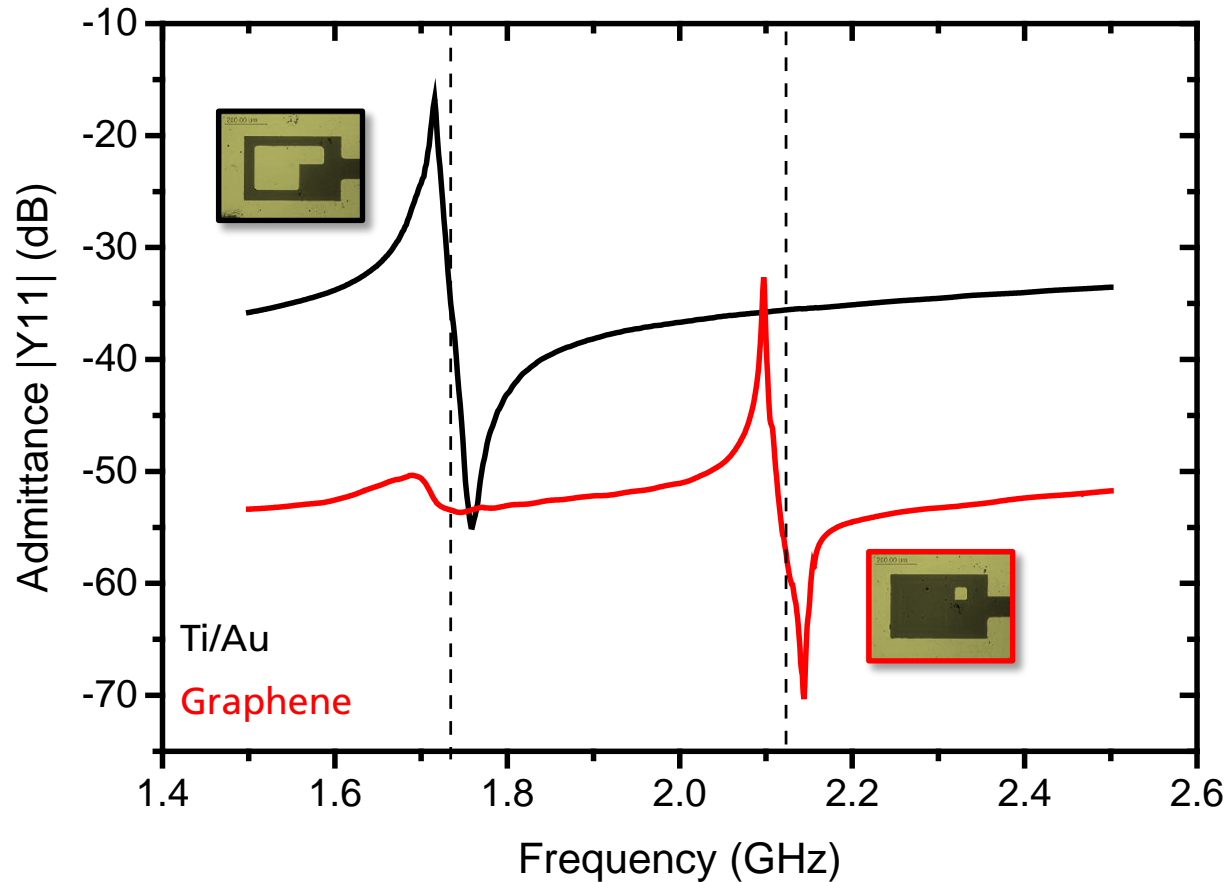
BAW-SMR device design



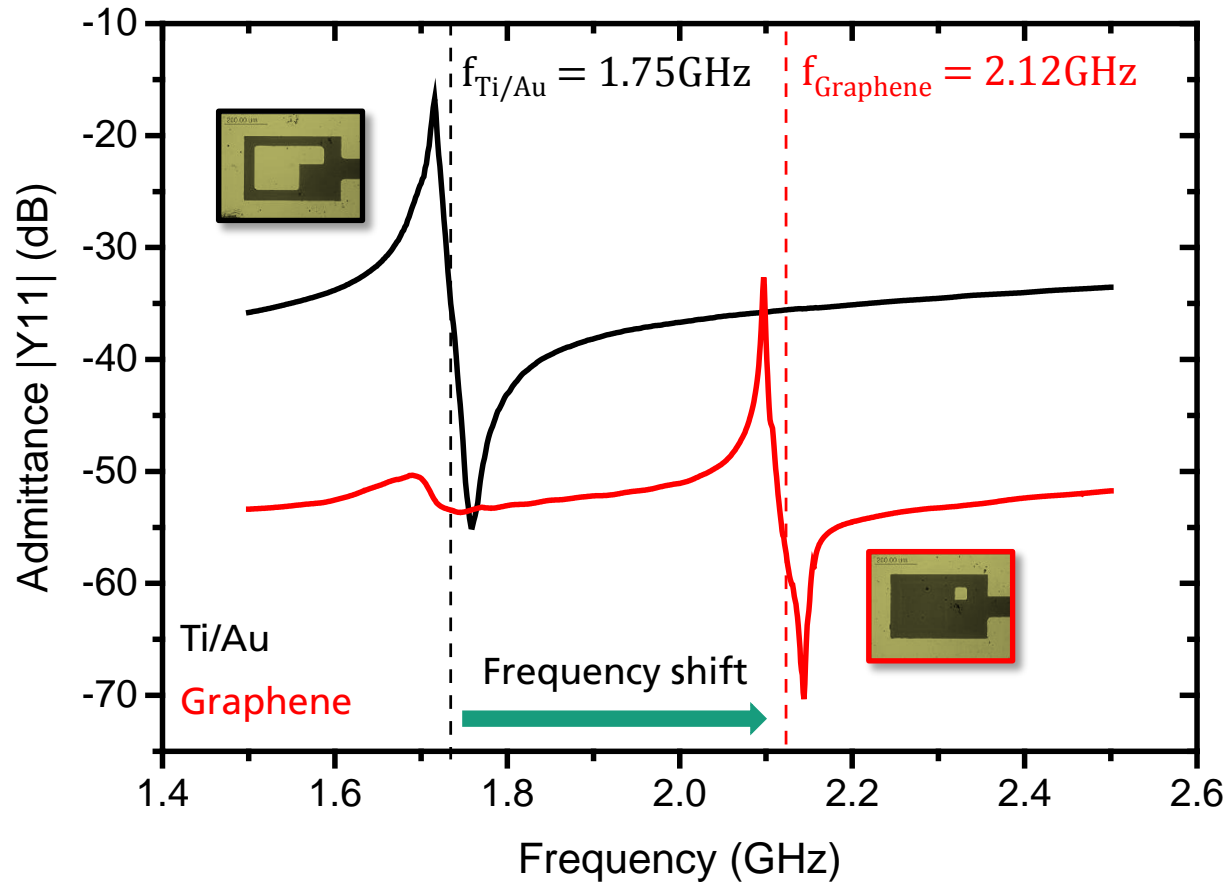
Mass reduction:
 $m_{Gr} = 0.00037 m_{Ti/Au}$
 resonator area:
 $200 \times 200 \mu\text{m}^2$



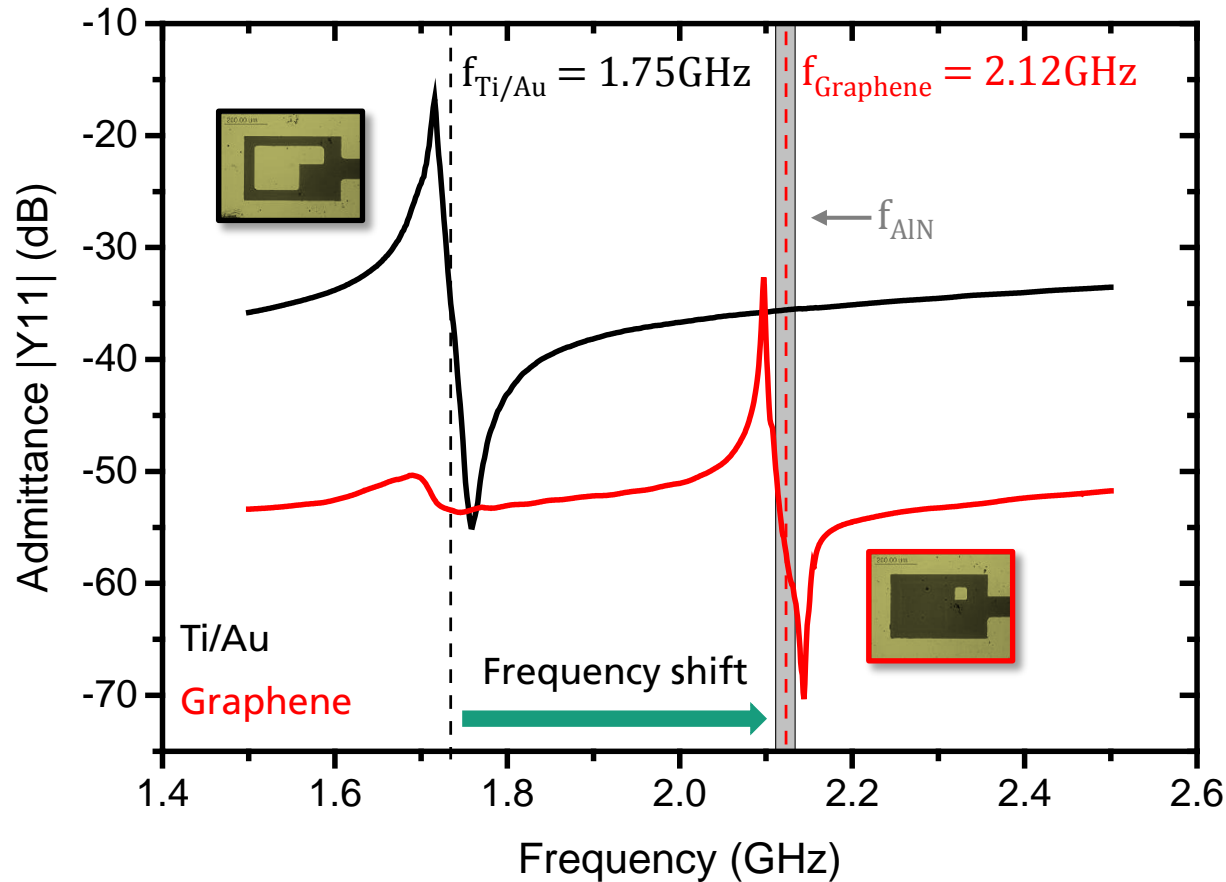
Electrical characterization – network analyser measurements



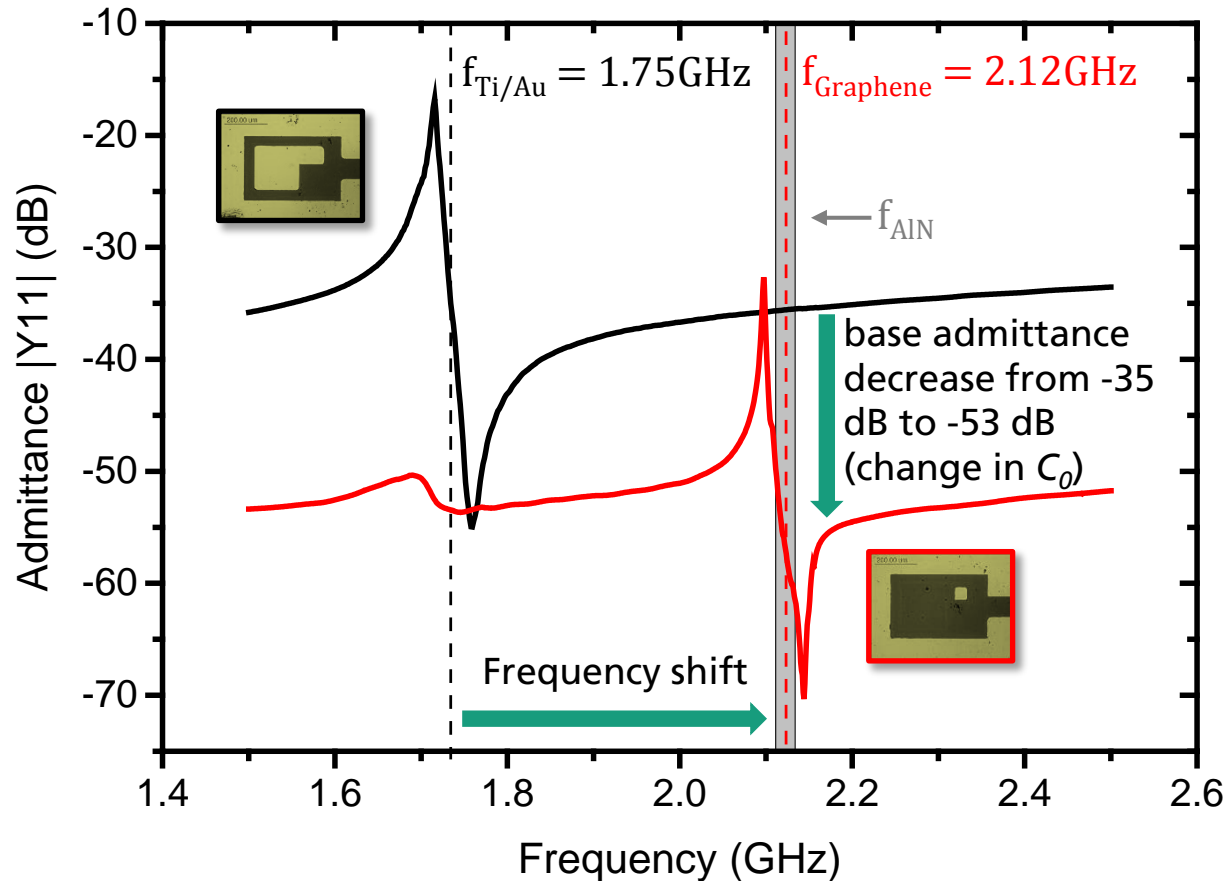
Electrical characterization – network analyser measurements



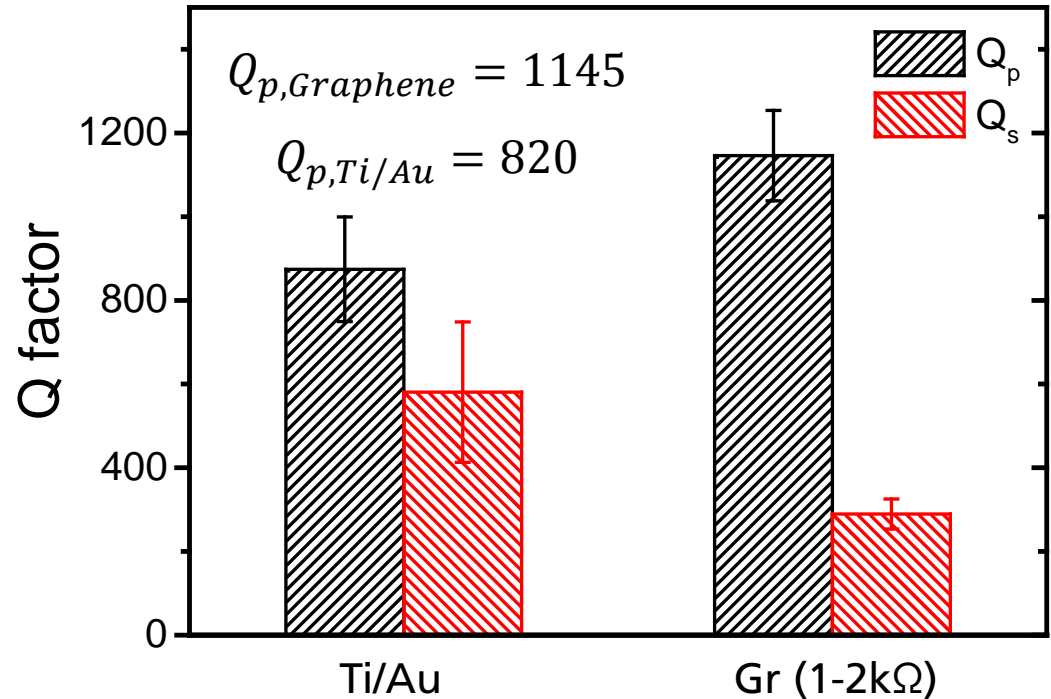
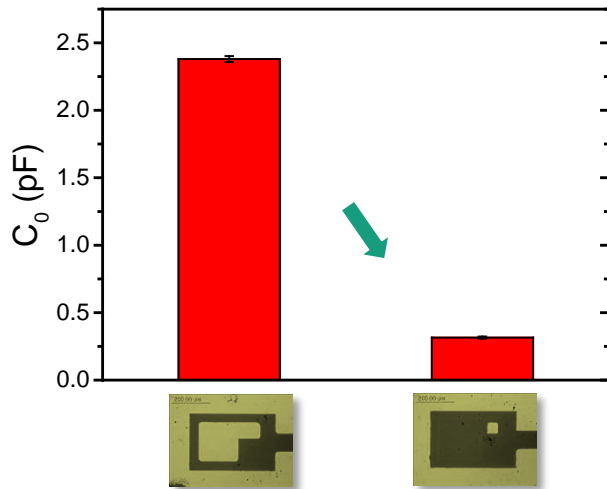
Electrical characterization – network analyser measurements



Electrical characterization – network analyser measurements

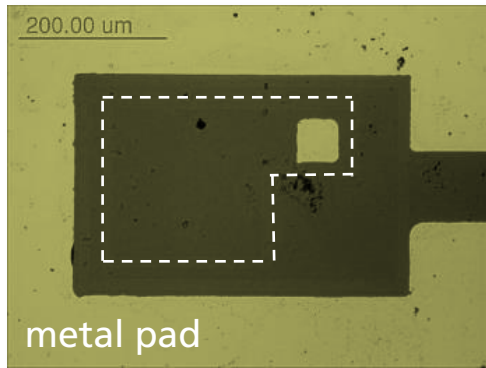


Determination of quality factor via fitting of equivalent circuit parameters

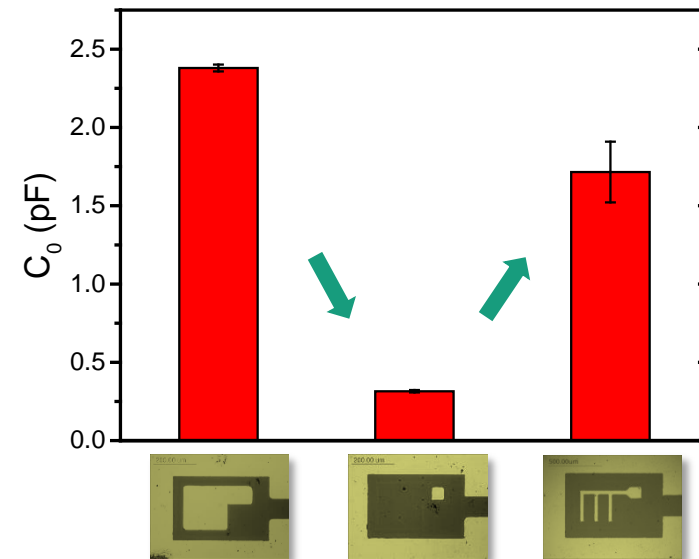
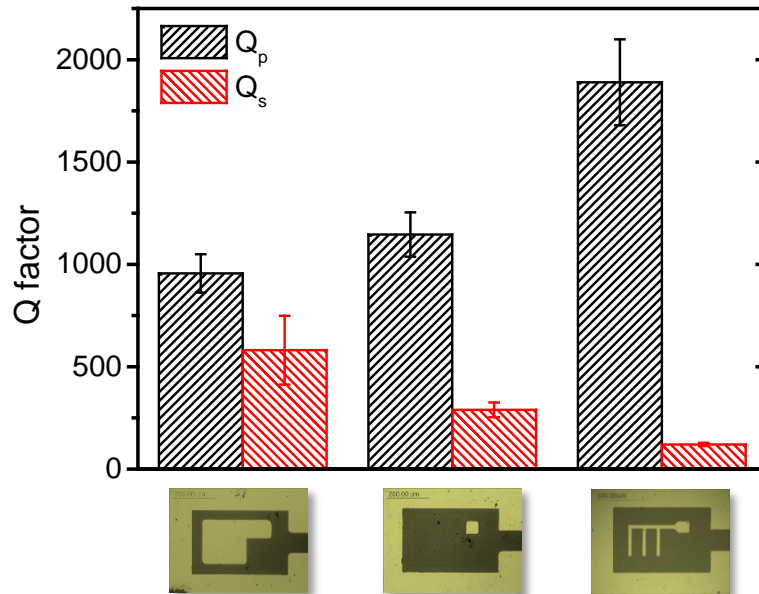
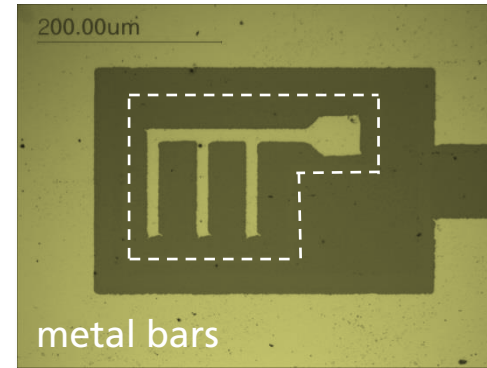


➔ Reduction of viscous losses!

Modifying electrode design



Increase of resonating graphene area



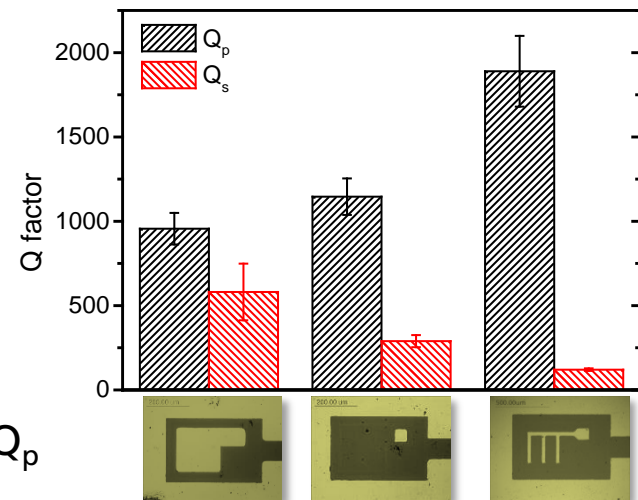
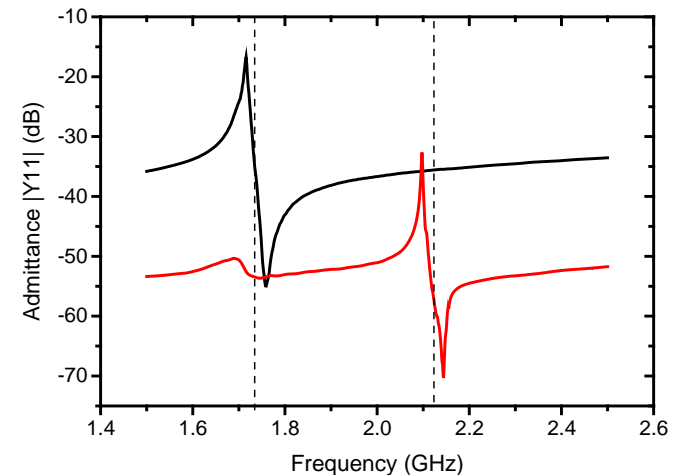
Summary

- Graphene avoids electrode induced frequency shift due to its virtually massless character
- Top electrode metal bar design increases resonating area (C_0)
- Viscous losses are strongly reduced resulting in a significantly increased Q factor for parallel resonance (Q_p)

Outlook

- Further improvements highly probable for graphene with $R_s \ll 2k\Omega$ regarding Q_s and Q_p

➔ Graphene doping, Multilayer graphene



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